

FIG. 1

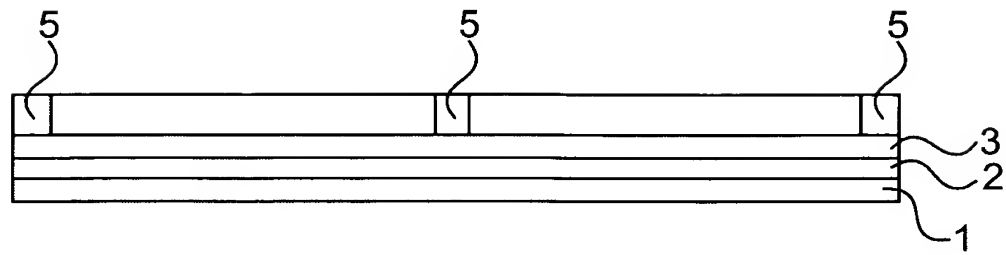


FIG. 2(a)

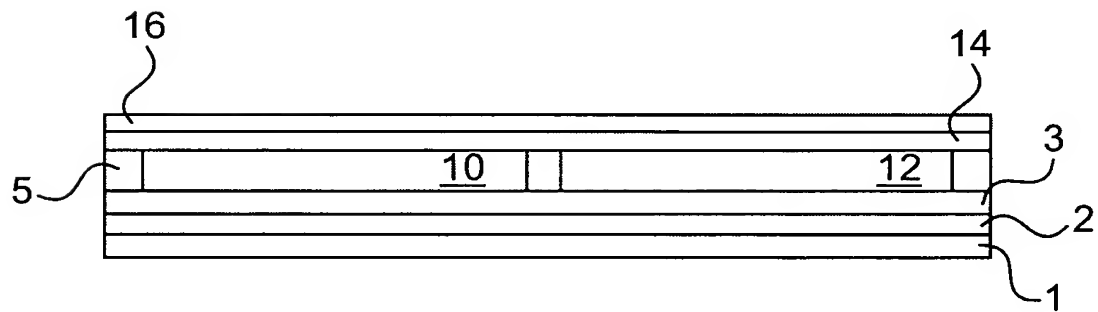


FIG. 2(b)

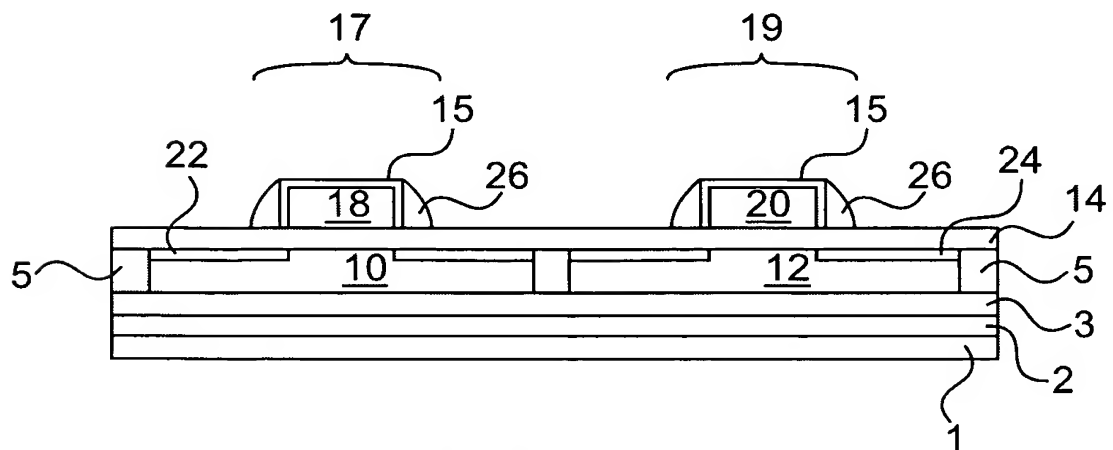


FIG. 2(c)

[illegible]

A cross-sectional view of a semiconductor device. The device consists of a substrate 1 with multiple layers 2 and 3. A conductive layer 5 is formed on the top surface of the substrate. On top of layer 5, there are several conductive regions 10, 12, and 15, which are separated by insulating regions 18 and 20. These regions are connected to a common conductive layer 30. A conductive layer 34 is formed on the top surface of the device, and a conductive layer 28 is formed on the bottom surface of the substrate. A conductive layer 22 is formed on the bottom surface of the substrate, and a conductive layer 36 is formed on the top surface of the device. A conductive layer 34 is also formed on the bottom surface of the substrate.

FIG. 2(f)

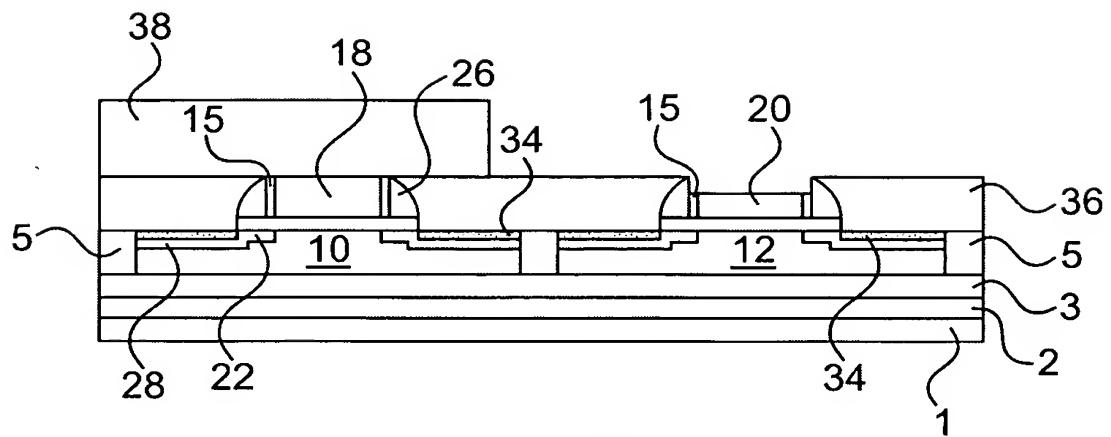


FIG. 2(g)

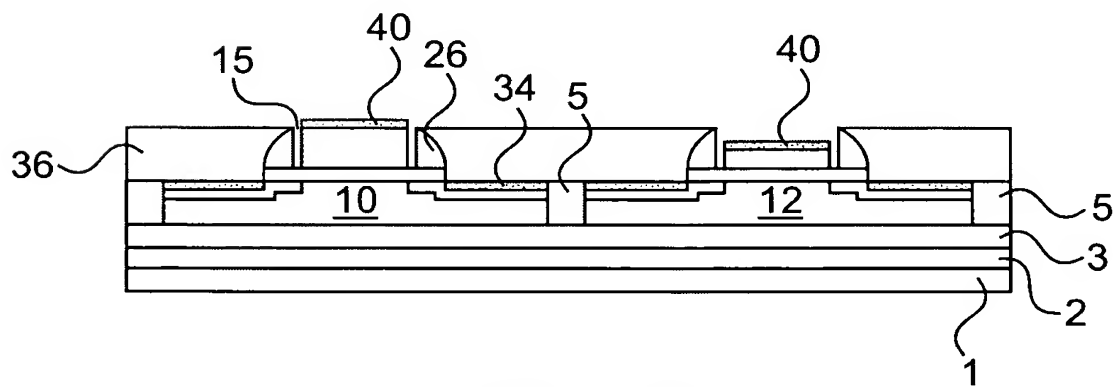


FIG. 2(h)

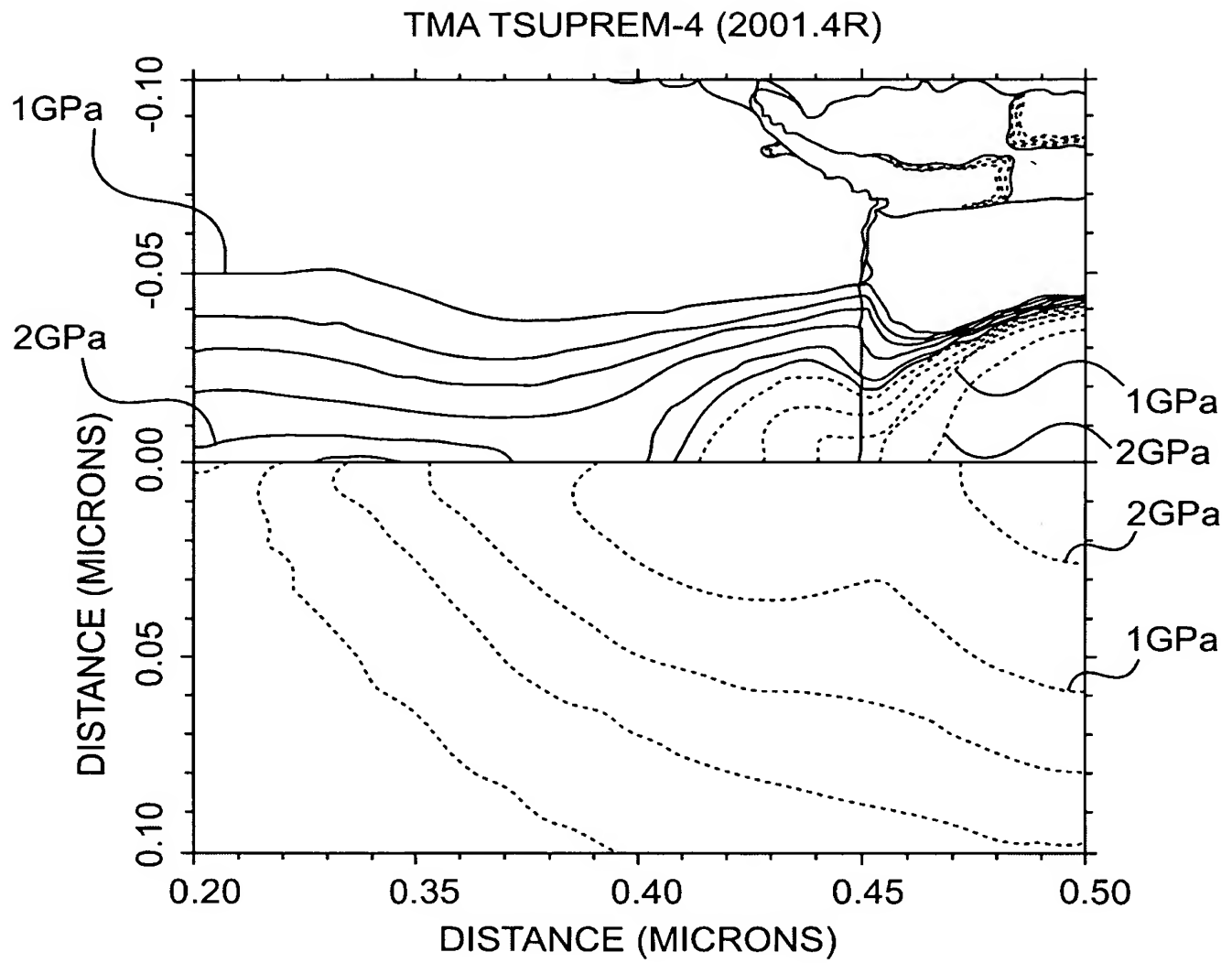


FIG. 3

..... TENSILE STRESS

——— COMPRESSIVE STRESS

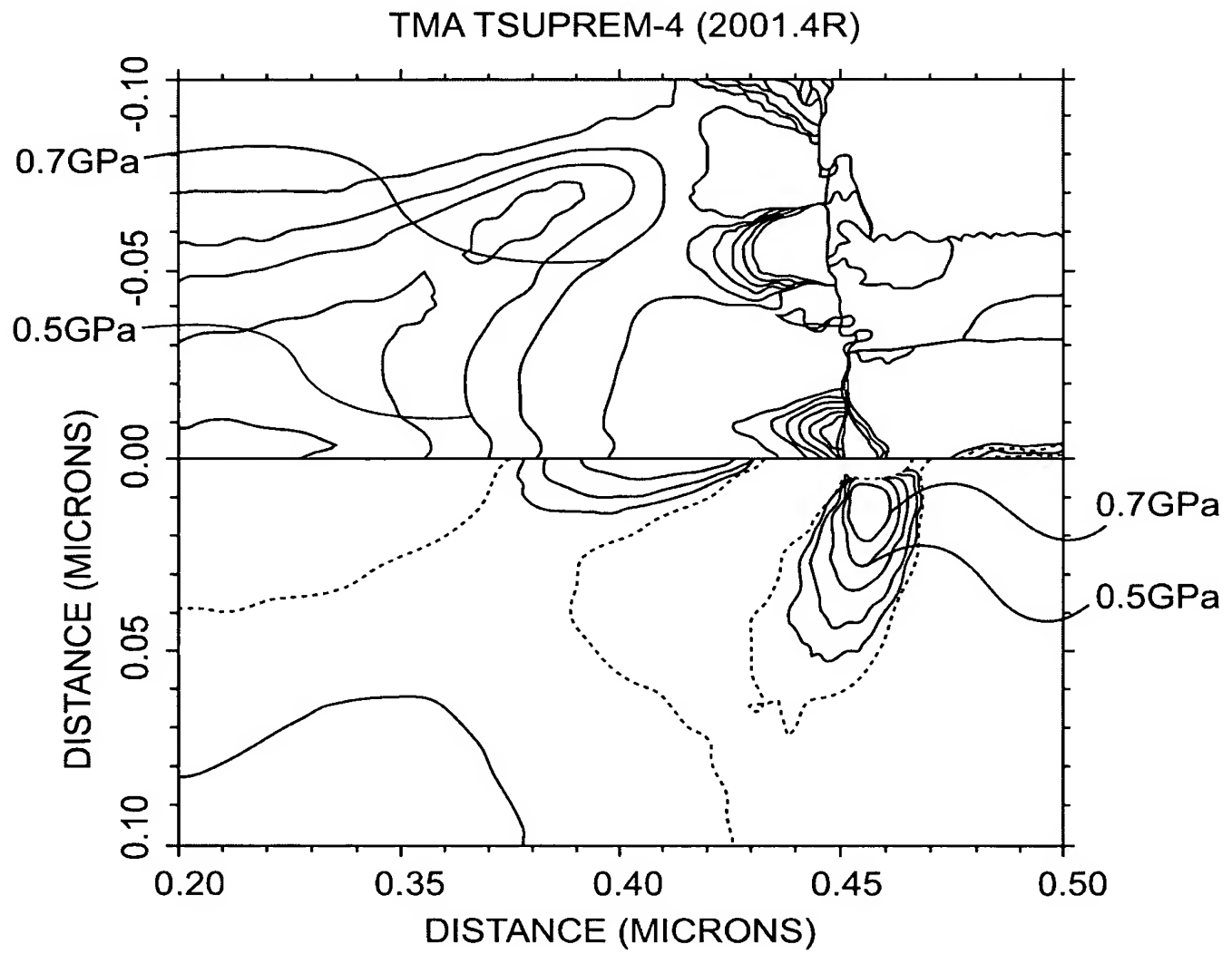


FIG. 4